

## SANYO Semiconductors

## DATA SHEET

An ON Semiconductor Company

**LV8413GP**—

# For DSC, and Cell Phone Camera Modules $H ext{-Bridge} imes 2 ext{-channel Motor Driver}$

#### Overview

The LV8413GP is an H-bridge  $\times$  2-channel motor driver IC and is able to control 4 modes of forward, reverse, brake, and standby.

**Bi-CMOS LSI** 

This IC housed in a miniature package is optimum for use in a stepping motor driving system for DSC or a camera module of cell phones.

#### **Features**

- Saturation drive H-bridge : 2-channels
- Built-in thermal protection circuit
- Built-in low voltage malfunction prevention circuit
- Incorporates a transistor for driving photosensors

#### **Specifications**

#### **Absolute Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Power supply voltage 1	VM max		6	V
Power supply voltage 2	V <sub>CC</sub> max		6	V
Output peak current	I <sub>O</sub> peak	Outs 1 to 4, $t \le$ 10msec, ON-duty $\le$ 20%	600	mA
Output continuous current 1	I <sub>O</sub> max1	Outs 1 to 4	400	mA
Output continuous current 2	I <sub>O</sub> max2	PI	15	mA
Allowable power dissipation	Pd max	Mounted on a circuit board*	0.7	W
Operating temperature	Topr		-20 to +85	°C
Storage temperature	Tstg		-55 to +150	°C

<sup>\*</sup> Specified circuit board :  $50.0 \text{mm} \times 40.0 \text{mm} \times 0.8 \text{mm}$  : glass epoxy four-layer board (2S2P)

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## LV8413GP

## Recommended Operating Conditions at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Power supply voltage range 1	VM		2.5 to 5.5	V
Power supply voltage range 2	VCC		2.5 to 5.5	V
Logic input voltage range	V <sub>IN</sub>		0 to V <sub>CC</sub> +0.3	V
Input frequency	f <sub>IN</sub>	IN1 to 4, INA	to 100	kHz

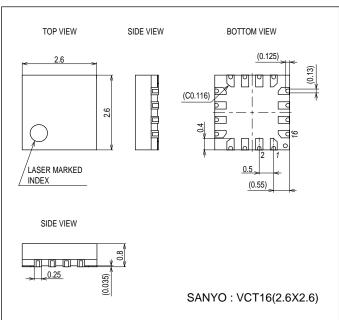
# $\textbf{Electrical Characteristics} \ at \ Ta = 25^{\circ}C, \ VM = 5V, \ V_{CC} = 3.3V, \ unless \ otherwise \ specified.$

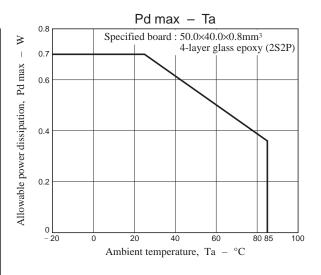
D	O: make al	Conditions	Ratings			
Parameter	Symbol		min	typ	max	Unit
Standby mode current drain	Istn	IN1 to 4 = "L"			1.0	μА
VM current drain	IM	Any one of IN1 to 4 = "H", with no load		70	150	μА
V <sub>CC</sub> current drain	<sup>I</sup> CC	Any one of IN1 to 4 = "H"		0.6	1.2	mA
V <sub>CC</sub> low-voltage cutoff voltage	VthV <sub>CC</sub>		1.85	2.10	2.35	V
Low-voltage hysteresis voltage	VthHYS		100	150	200	mV
Thermal shutdown temperature	TSD	Design guarantee value *	160	180	200	°C
Thermal hysteresis width	ΔTSD	Design guarantee value *	10	30	50	°C
OUT1 to 4						
Logic pin internal pull-down resistance	Rin	IN1 to 4	50	100	200	kΩ
Logic pin input current	linL	V <sub>IN</sub> = 0, IN1 to 4			1.0	μА
	linH	V <sub>IN</sub> = 3.3V, IN1 to 4	20	33	60	μА
Logic input high-level voltage	VinH	IN1 to 4	2.5			V
Logic input low-level voltage	VinL	IN1 to 4			1.0	V
Output on-resistance	Ronu	I <sub>O</sub> = 400mA, upper ON resistance		0.5	0.8	Ω
	Rond	I <sub>O</sub> = 400mA, lower ON resistance		0.3	0.5	Ω
Output leakage current	l <sub>O</sub> leak				1	μА
Diode forward voltage	VD	ID = -400mA		1.0		V
PI	•	•				
Logic pin internal pull-down resistance	Rin	INA	50	100	200	kΩ
Logic pin input current	linL	V <sub>IN</sub> = 0, INA			1.0	μА
	linH	V <sub>IN</sub> = 3.3V, INA	20	33	50	μА
Logic input high-level voltage	VinH	INA	2.5			V
Logic input low-level voltage	VinL	INA			1.0	V
Output on-resistance	Ron	I <sub>O</sub> = 10mA		4	6	Ω
Output leakage current	l <sub>O</sub> leak			Ì	1	μА

#### **Package Dimensions**

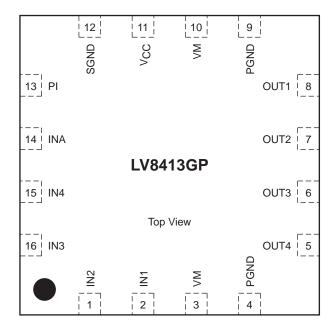
unit: mm (typ)

3318

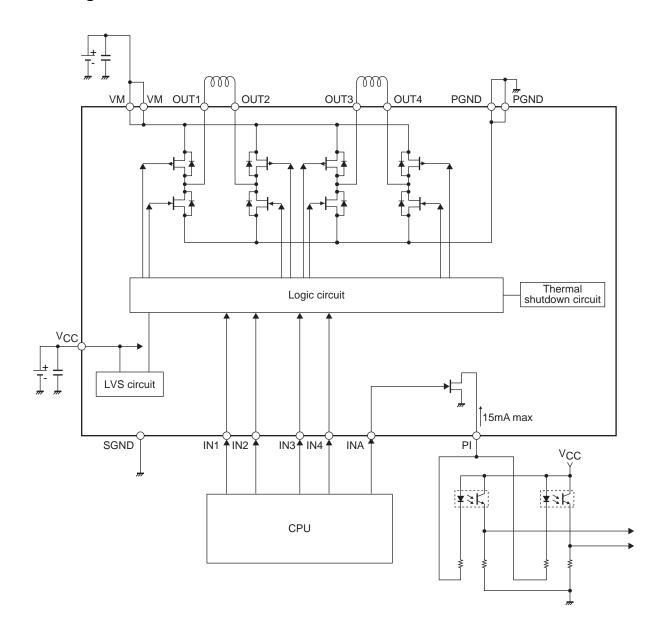




## **Pin Assignment**



## **Block Diagram**



### **Pin Functions**

Pin No.	Pin name	Pin Function	Equivalent Circuit
2 1 16 15 14	IN1 IN2 IN3 IN4 INA	Control signal input pin	Vcc O
			10kΩ 100kΩ GND
8 7	OUT1 OUT2	Outpin Outpin	VM
6	OUT3 OUT4	Outpin Outpin	Y
13	PI	Outpin	PGND
13	PI	Оцріп	GND
11	VCC	Logic system power supply connection pin	
3	VM	Motor power supply connection pin	
10	VM	Motor power supply connection pin	
12	SGND	Signal ground	
4	PGND	Power ground	
9	PGND	Power ground	

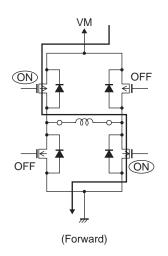
#### Logic input specifications

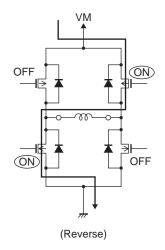
• Common channels 1 to 2

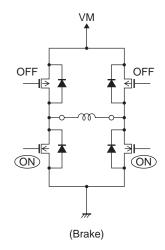
ch1: IN1 to IN2, OUT1 to OUT2 ch2: IN3 to IN4, OUT3 to OUT4

Input		Output		On another manda	
IN1	IN2	OUT1	OUT2	Operation mode	
L	L	OFF	OFF	Standby	
Н	L	Н	L	CW (forward)	
L	Н	L	Н	CCW (reverse)	
Н	Н	L	L	Brake	

• Output stage transistor function







• Photo sensor driving transistor

When thermal shutdown and V<sub>CC</sub> low-voltage cut circuits are activated, OUT1 through OUT4 are turned OFF under control of the internal circuit. But the output (PI) of photo sensor driving transistor continues operation.

Input	Photo sensor driving
INA	PI
L	OFF
Н	ON

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